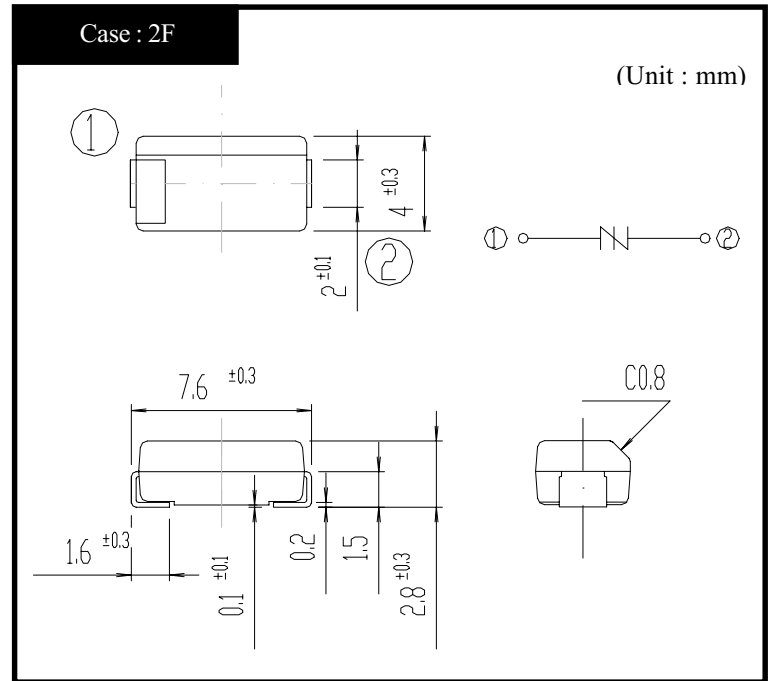


KP4N12

OUTLINE DIMENSIONS



RATINGS

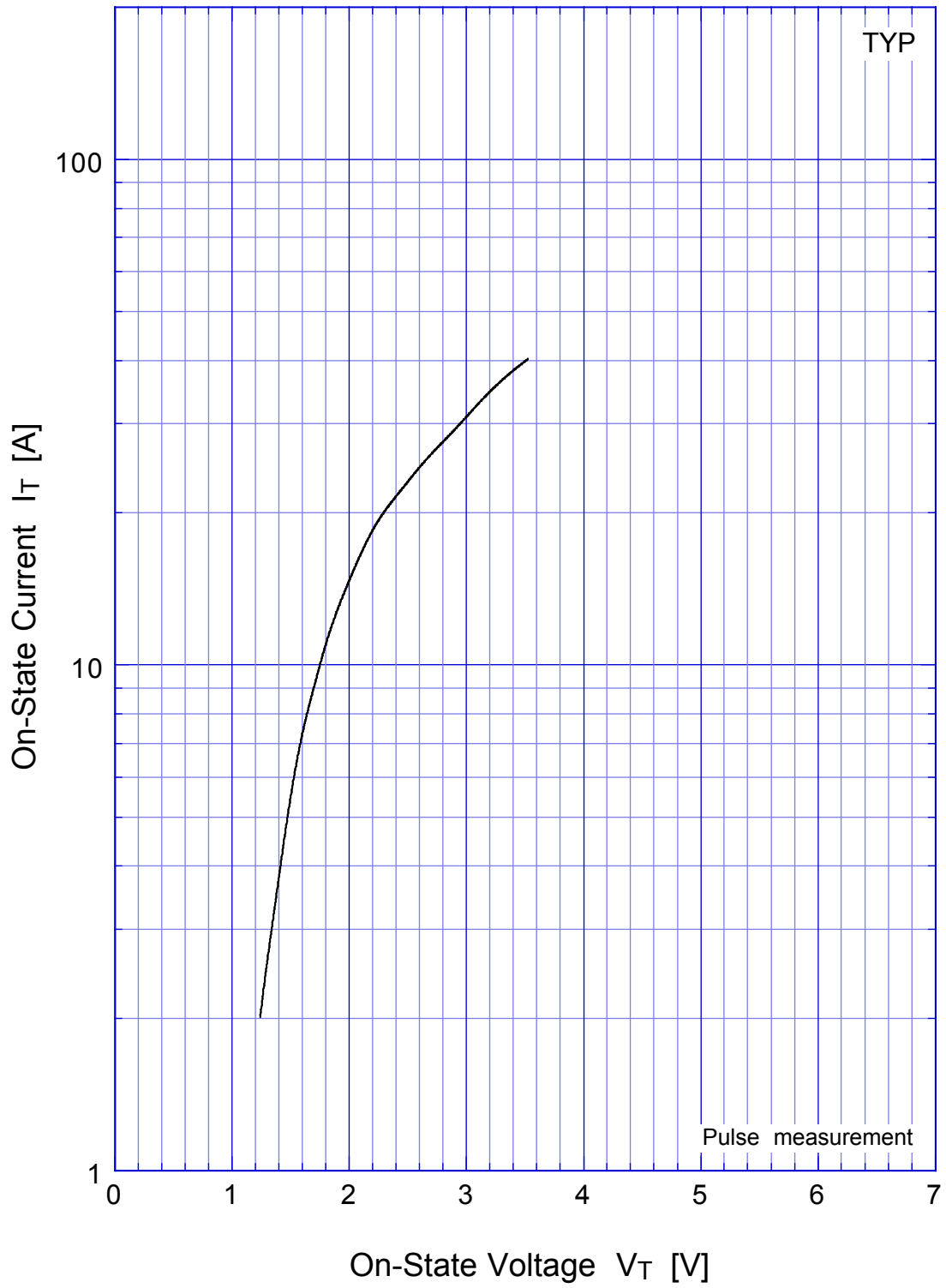
● Absolute Maximum Ratings

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	T_{stg}		-40~125	°C
Junction Temperature	T_j		125	°C
Maximum Off-State Voltage	V_{DRM}		100	V
Surge On-State Current	I_{TSM}	10/1000 μ s, Non-repetitive	40	A
		10/200 μ s, Non-repetitive	60	
		8/20 μ s, Non-repetitive	150	

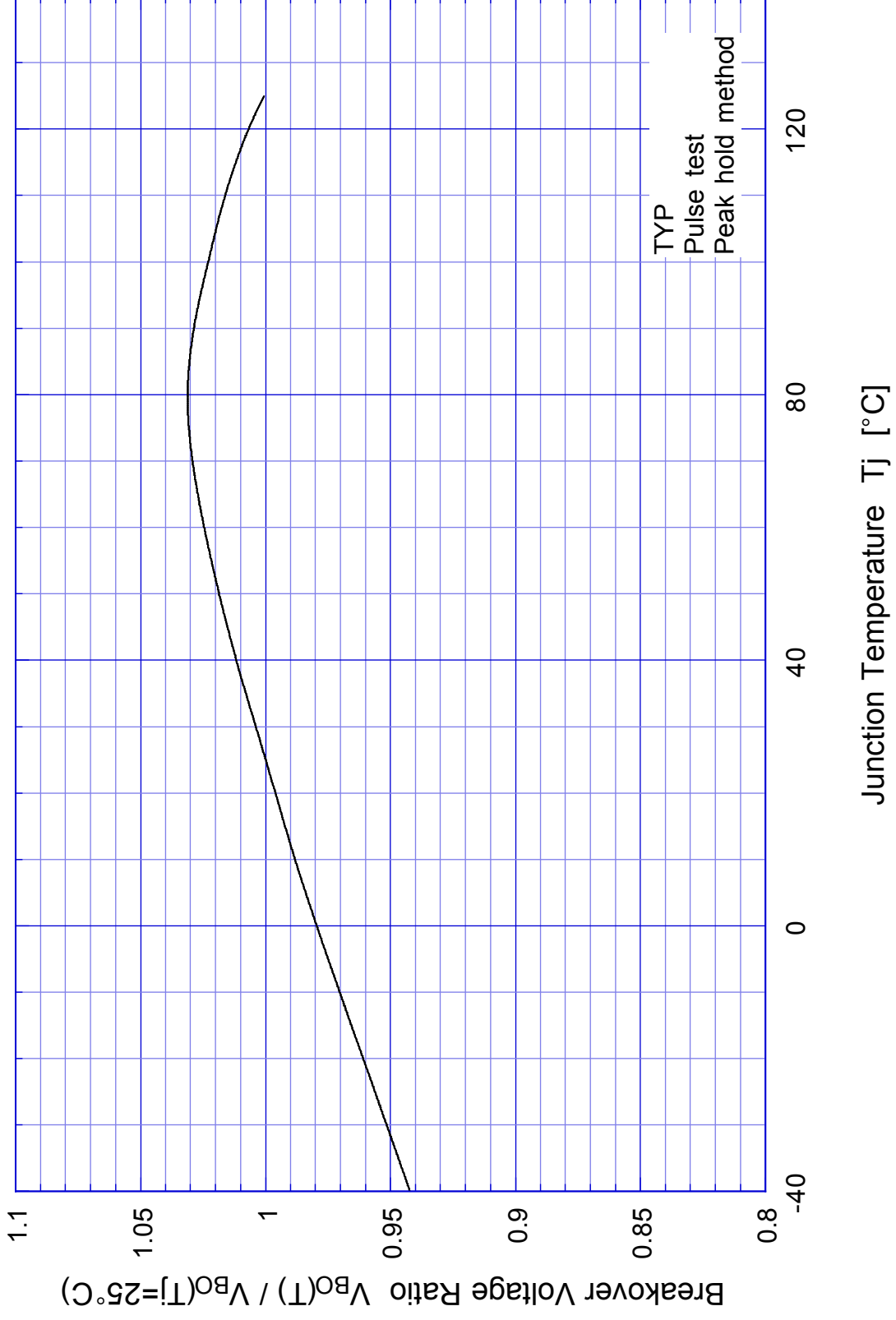
● Electrical Characteristics (Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Breakover Voltage	V_{BO}	Pulse measurement (Peak hold)	Min 110	V
Off-State Current	I_{DRM}	$V_D = V_{DRM}$	Max 10	μ A
Holding Current	I_H	Pulse measurement	Min 100	mA
On-State Voltage	V_T	$I_T = 2A$	TYP 1.25	V
Junction Capacitance	C_j	f = 1kHz OSC = 1V, $V_D = 50V$	Max 50	pF
Clamping Voltage	V_{CL}	$dv/dt = 100V/\mu s$	Max 135	V

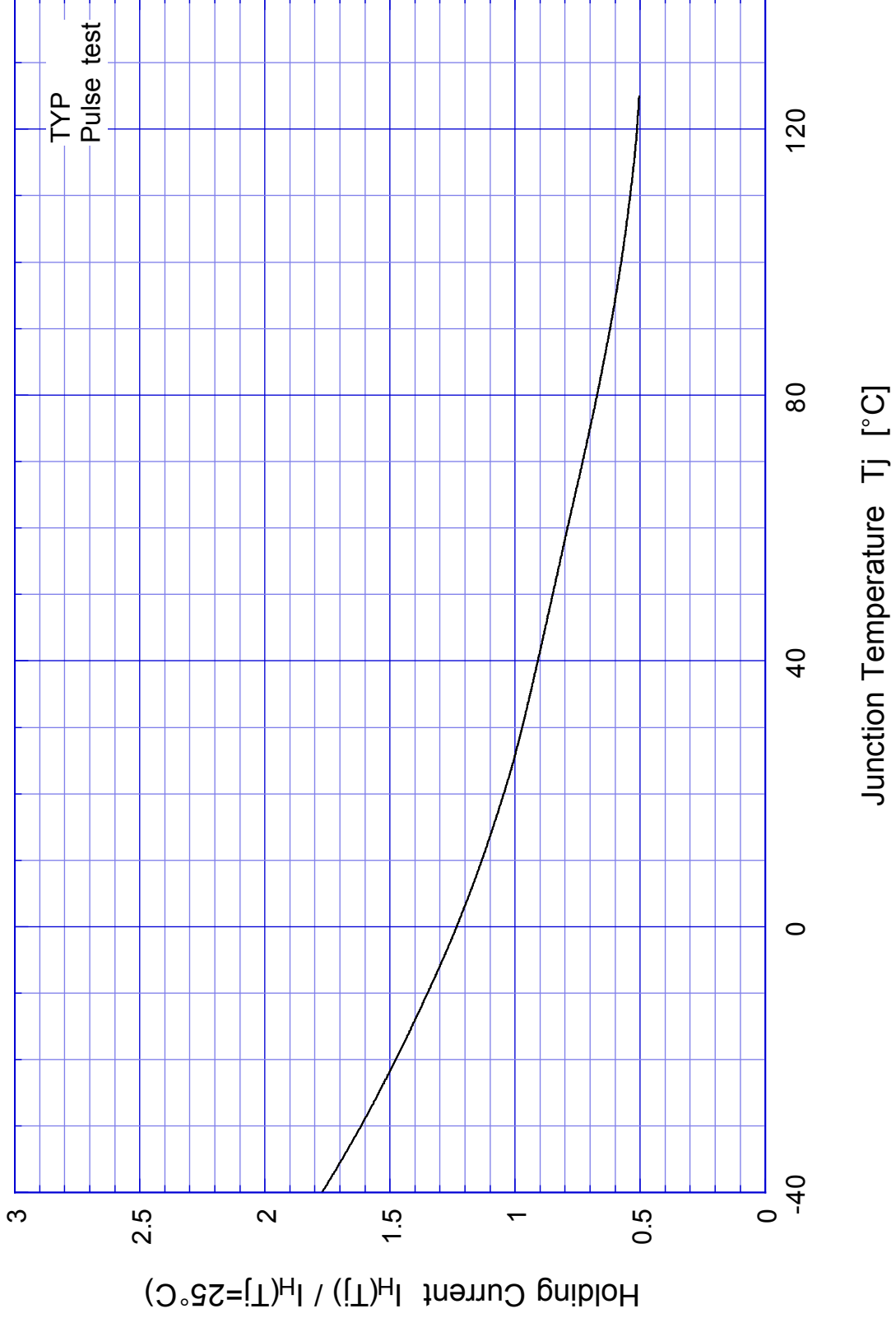
KP4N12 On-State Voltage - On-State Current



KP4N12 Breakover Voltage - Junction Temperature

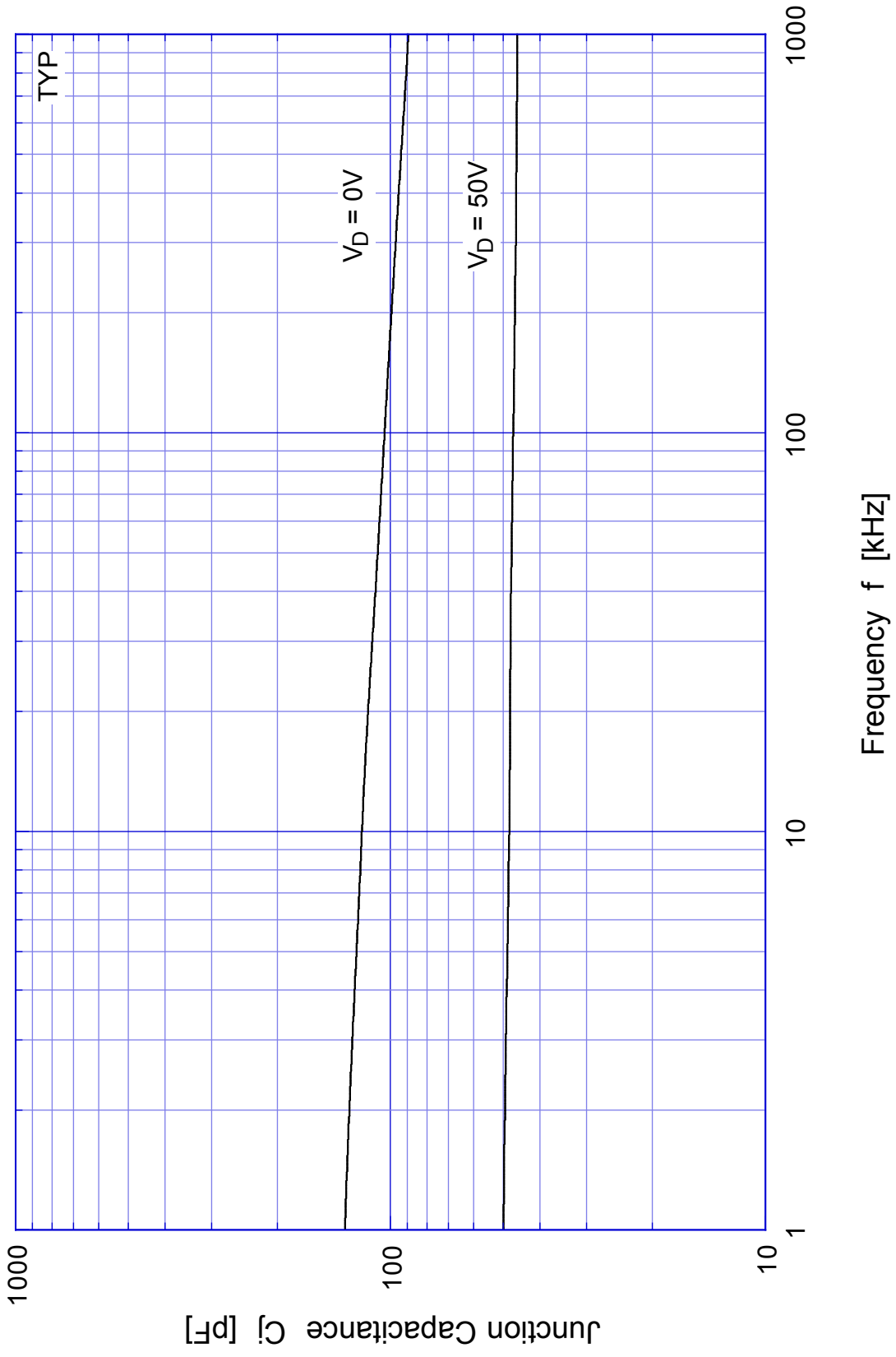


KP4N12 Holding Current - Junction Temperature



KP4N12

Junction Capacitance

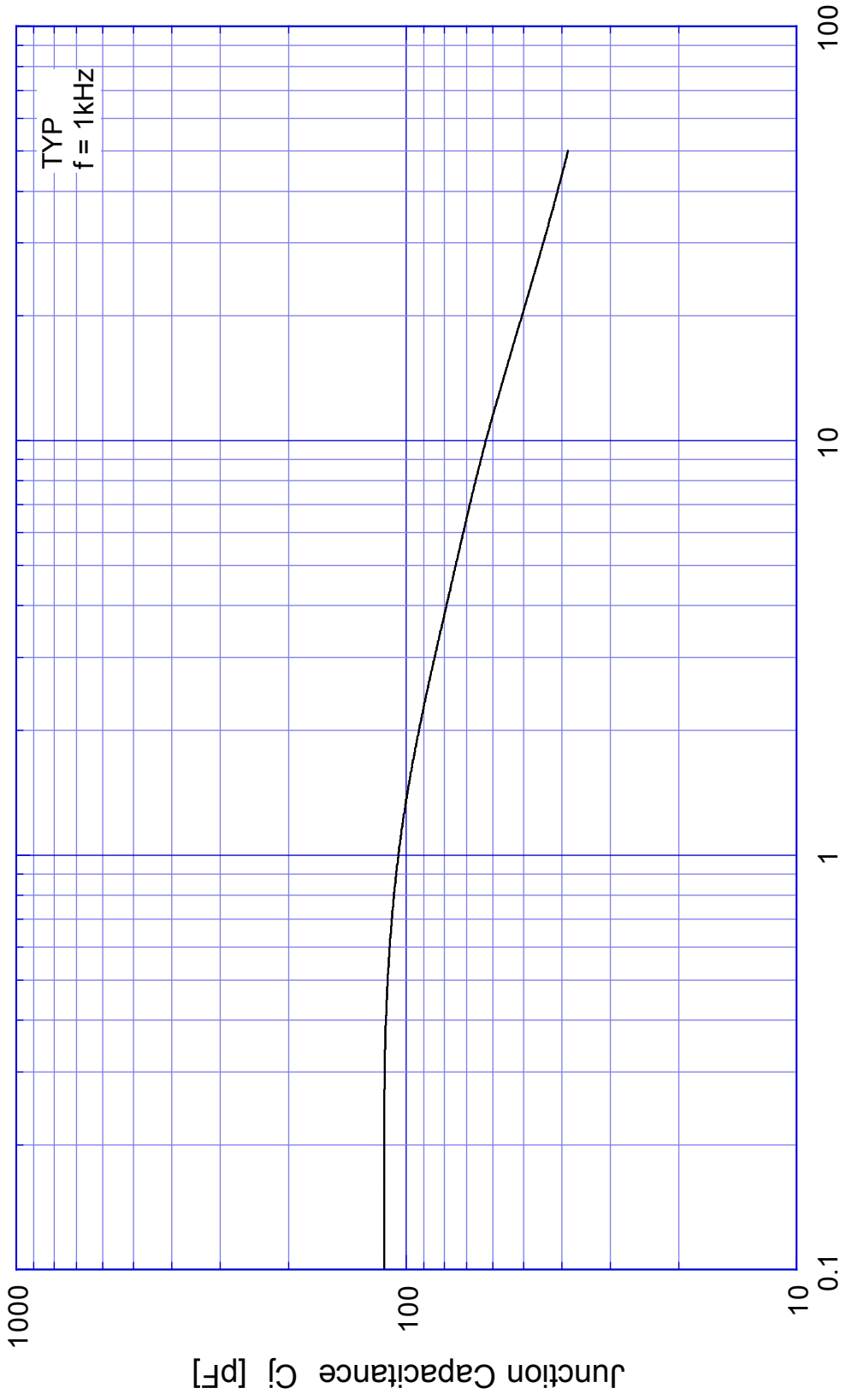


TYP

$V_D = 0V$

$V_D = 50V$

KP4N12 Junction Capacitance



Off-State Applied Voltage V_D [V]